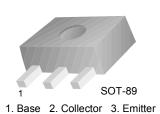
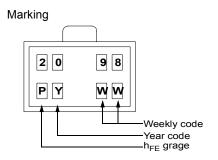


# FJC2098 NPN Epitaxial Silicon Transistor

## **Camera Strobe Flash Application**

- Complement to FJC1386
- · High Collector Current
- Low Collector-Emitter Saturation Voltage





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	50	V
$V_{CEO}$	Collector-Emitter Voltage	20	V
$V_{EBO}$	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current (DC)	5	A
P <sub>C</sub>	Power Dissipation(T <sub>C</sub> =25°C)	0.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics TC=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 50\mu A, I_E = 0$	50			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0	20			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 50\mu A, I_C = 0$	6			V
I <sub>CEO</sub>	Collector Cut-off Current	$V_{CE} = 40V, V_{B} = 0$			0.5	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0			0.5	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 2V, I_{C} = 0.5A$	120		390	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A, I <sub>B</sub> = 0.1A			1.0	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A, I <sub>B</sub> = 0.1A			1.2	V
C <sub>OB</sub>	Collector Output Capacitance	V <sub>CB</sub> = 20V, I <sub>E</sub> = 0, f = 1MHz		23		pF

# h<sub>FE</sub> Classification

Classification	Q	R	
h <sub>FE</sub>	120 ~ 270	180 ~ 390	

# Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
2098 FJC2098		SOT-89	13"		4,000

### **Typical Performance Characteristics**

Figure 1. Static Characteristic

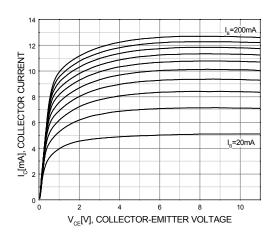


Figure 2. DC Current Gain

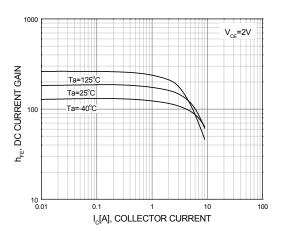


Figure 3. Collector-Emitter Saturation Voltage

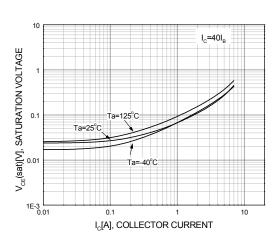


Figure 4. Base-Emitter Saturation Voltage

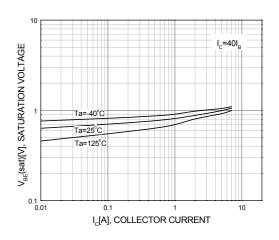


Figure 5. Base-Emitter On Voltage

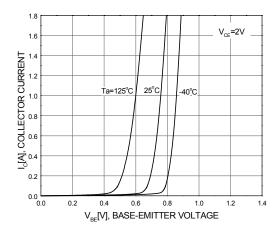
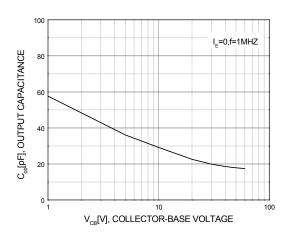
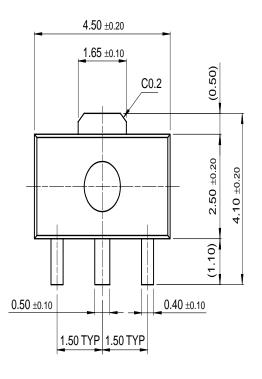


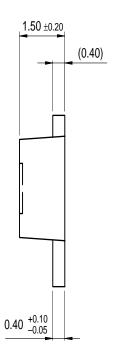
Figure 6. Common-Base Open-Circuit Output Capacitance

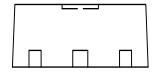


## **Mechanical Dimensions**

# **SOT-89**







**Dimensions in Millimeters** 

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

SuperSOT™-6

### **PRODUCT STATUS DEFINITIONS**

### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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